General Description

OST25N120KEWF uses advanced Oriental-Semi's patented Trident-Gate Bipolar Transistor (TGBT™) technology to provide extremely low V_{CE}(sat), low gate charge, and excellent switching performance. This device is suitable for mid to high range switching frequency converters.

Features

- Advanced TGBT™ technology
- Excellent conduction and switching loss
- Excellent stability and uniformity
- Fast and soft antiparallel SiC diode

RoHS compliant

Applications

- Induction converters
- Uninterruptible power supplies

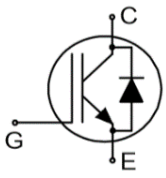
Key Performance Parameters

Parameter	Value	Unit
$V_{CES, min}$ @ 25 °C	1200	V
Maximum junction temperature	175	°C
$I_{C, pulse}$	100	A
$V_{CE(sat), typ}$ @ V_{GE}=15 V	1.75	V
Q_g	77	nC

Marking Information

Product Name	Package	Marking
OST25N120KEWF	TO263	OST25N120KEW

Package & Pin Information



Absolute Maximum Ratings at T_{vj}=25 °C unless otherwise noted

Parameter	Symbol	Value	Unit
Collector emitter voltage	V_{CES}	1200	V
Gate emitter voltage	V_{GES}	±20	V
Transient gate emitter voltage, T_P≤10 μs, D<0.01		±30	V
Continuous collector current[1], T_C=25 °C	I_C	40	A
Continuous collector current[1], T_C=100 °C		25	A
Pulsed collector current[2], T_C=25 °C	$I_{C,\ pulse}$	100	A
Diode forward current[1], T_C=25 °C	I_F	40	A
Diode forward current[1], T_C=100 °C		25	A
Diode pulsed current[2], T_C=25 °C	$I_{F,\ pulse}$	100	A
Power dissipation[3], T_C=25 °C	P_D	200	W
Power dissipation[3], T_C=100 °C		100	W
Operation and storage temperature	T_{stg}, T_{vj}	-55 to 175	°C

Thermal Characteristics

Parameter	Symbol	Value	Unit
IGBT thermal resistance, junction-case	$R_{\theta JC}$	0.75	°C/W
Diode thermal resistance, junction-case	$R_{\theta JC}$	0.85	°C/W
Thermal resistance, junction-ambient[4]	$R_{\theta JA}$	40	°C/W

Electrical Characteristics at T_{vj}=25 °C unless otherwise specified

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test condition
Collector-emitter breakdown voltage	$V_{(BR)CES}$	1200			V	V_{GE}=0 V, I_C=0.5 mA
Collector-emitter saturation voltage	$V_{CE(sat)}$		1.75	2.5	V	V_{GE}=15 V, I_C=25 A T_{vj}=25 °C
			2.22		V	V_{GE}=15 V, I_C=25 A, T_{vj}=125 °C
			2.49		V	V_{GE}=15 V, I_C=25 A, T_{vj}=175 °C
Gate-emitter threshold voltage	$V_{GE(th)}$	5.0	5.5	6.0	V	V_{CE}=V_{GE}, I_D=0.5 mA
Diode forward voltage	V_F		1.85	2.5	V	V_{GE}=0 V, I_F=25 A T_{vj}=25 °C
			2.6		V	V_{GE}=0 V, I_F=25 A, T_{vj}=125 °C
			3.17		V	V_{GE}=0 V, I_F=25 A, T_{vj}=175 °C
Gate-emitter leakage current	I_{GES}			100	nA	V_{CE}=0 V, V_{GE}=20 V
Zero gate voltage collector current	I_{CES}			100	μA	V_{CE}=1200 V, V_{GE}=0 V

Dynamic Characteristics

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test condition
Input capacitance	C_{ies}		5557		pF	V_{GE}=0 V, V_{CE}=25 V, f=100 kHz
Output capacitance	C_{oes}		288		pF	
Reverse transfer capacitance	C_{res}		5		pF	
Turn-on delay time	$t_{d(on)}$		39		ns	V_{GE}=15 V, V_{CC}=600 V, R_G=10 Ω, I_C=25 A
Rise time	t_r		27		ns	
Turn-off delay time	$t_{d(off)}$		100		ns	
Fall time	t_f		87		ns	
Turn-on energy	E_{on}		0.53		mJ	
Turn-off energy	E_{off}		0.64		mJ	
Turn-on delay time	$t_{d(on)}$		37		ns	V_{GE}=15 V, V_{CC}=600 V, R_G=10 Ω, I_C=12.5 A
Rise time	t_r		14		ns	
Turn-off delay time	$t_{d(off)}$		115		ns	
Fall time	t_f		85		ns	
Turn-on energy	E_{on}		0.22		mJ	
Turn-off energy	E_{off}		0.31		mJ	

Gate Charge Characteristics

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test condition
Total gate charge	Q_g		77		nC	V_{GE}=15 V, V_{CC}=960 V, I_C=25 A
Gate-emitter charge	Q_{ge}		43		nC	
Gate-collector charge	Q_{gc}		9		nC	

Body Diode Characteristics

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test condition
Diode reverse recovery time	t_{rr}		28		ns	V_R=600 V, I_F=25 A, di_F/dt=500 A/μs T_{vj}=25 °C
Diode reverse recovery charge	Q_{rr}		60		nC	
Diode peak reverse recovery current	I_{rrm}		3.3		A	

Note

1) Calculated continuous current based on maximum allowable junction temperature.
2) Repetitive rating; pulse width limited by max. junction temperature.
3) Pd is based on max. junction temperature, using junction-case thermal resistance.
4) The value of $R_{\theta JA}$ is measured with the device mounted on 1 in^2 FR-4 board with 2oz. Copper, in a still air environment with T_a=25 °C.

Electrical Characteristics Diagrams

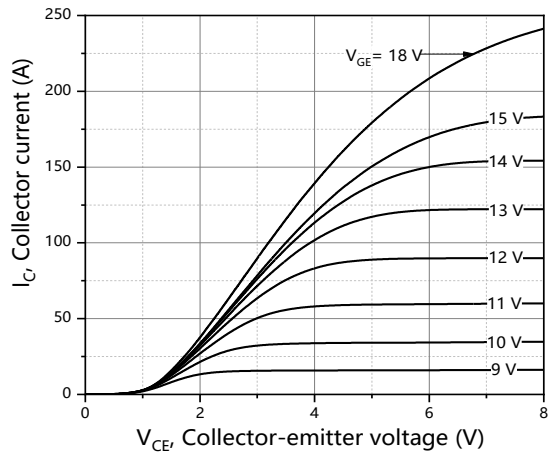


Figure 1. Typical output characteristics
(T_{vj}=25 °C)

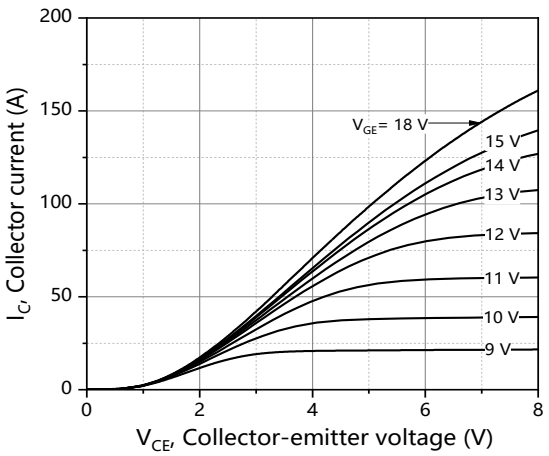


Figure 2. Typical output characteristics
(T_{vj}=150 °C)

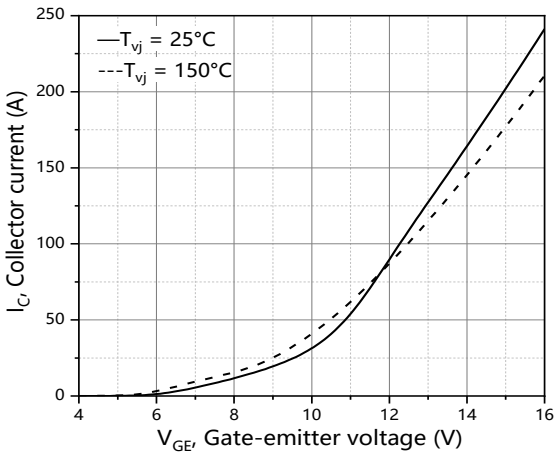


Figure 3. Typical transfer characteristics
(V_{CE}=20 V)

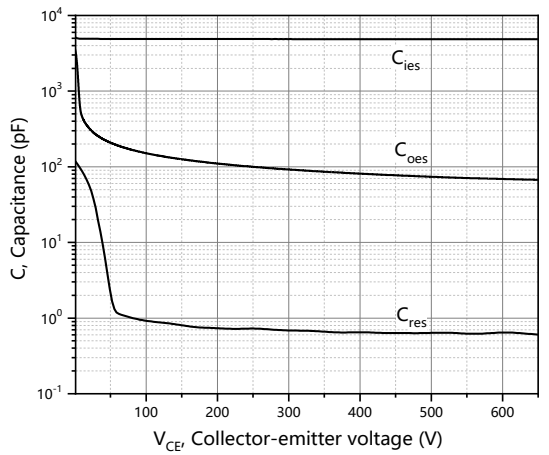


Figure 4. Typical capacitance
(V_{GE}=0V, f=100 kHz)

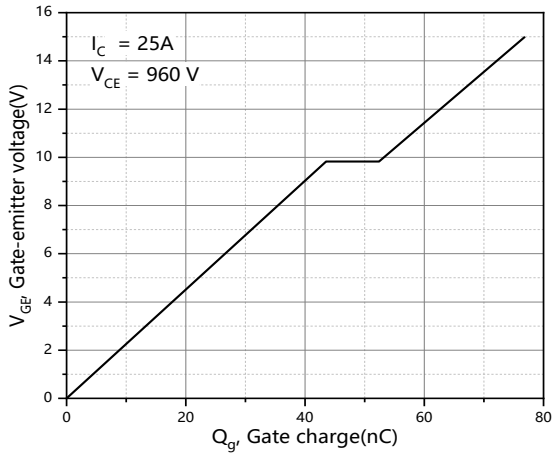


Figure 5. Typical gate charge

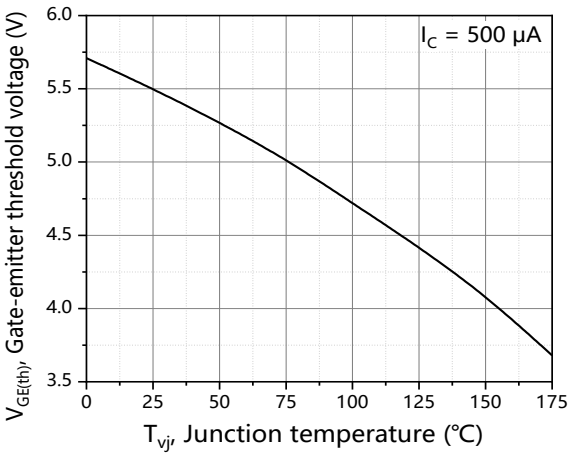


Figure 6. Gate-emitter threshold voltage

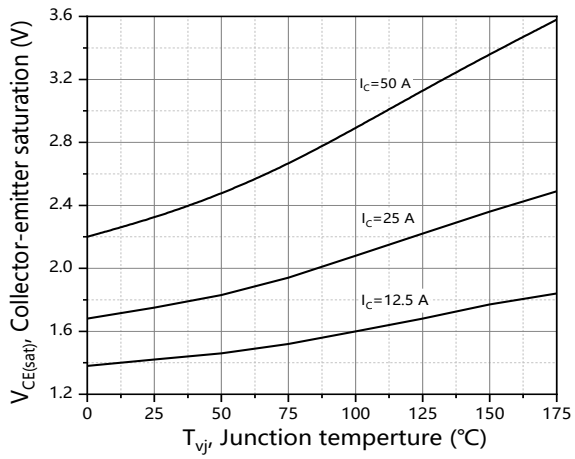


Figure 7. Typical collector-emitter voltage

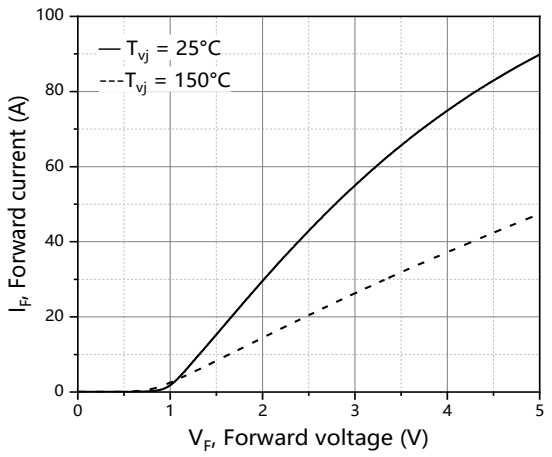


Figure 8. Forward characteristic of diode

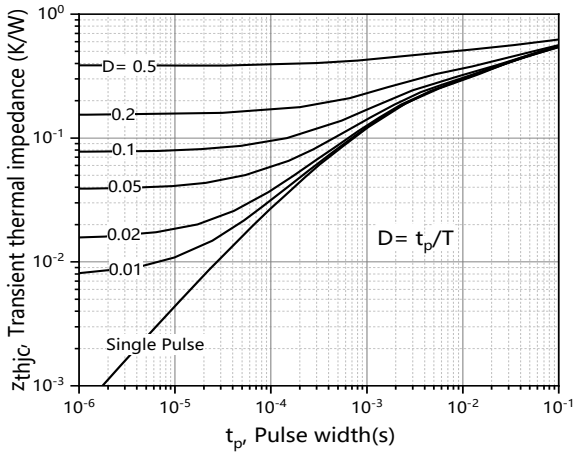


Figure 9. IGBT transient thermal impedance

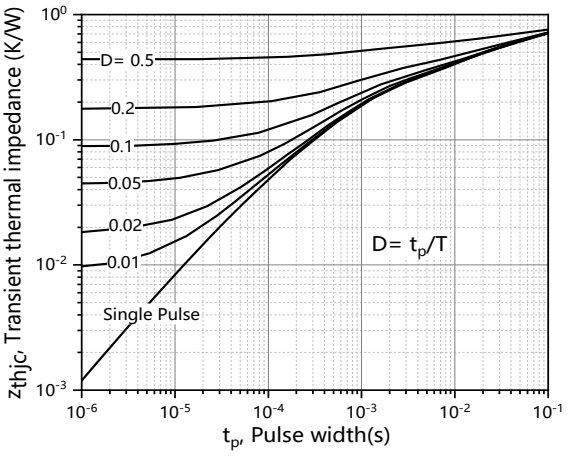


Figure 10. Diode transient thermal impedance

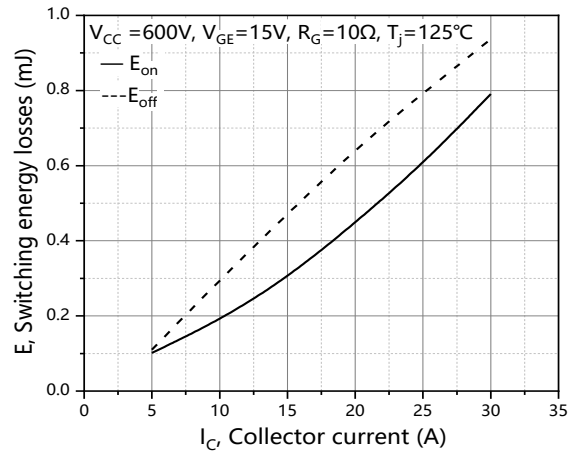


Figure 11. Switching energy vs. collector current

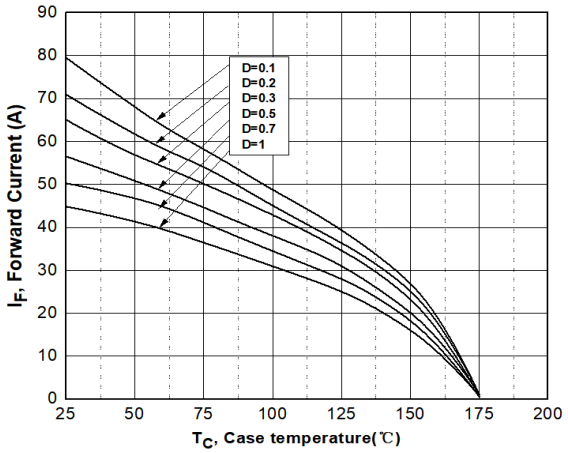


Figure 12. Peak forward current versus case tempertrature

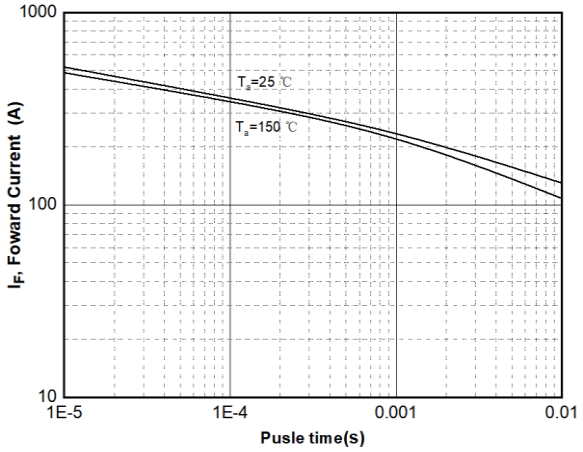
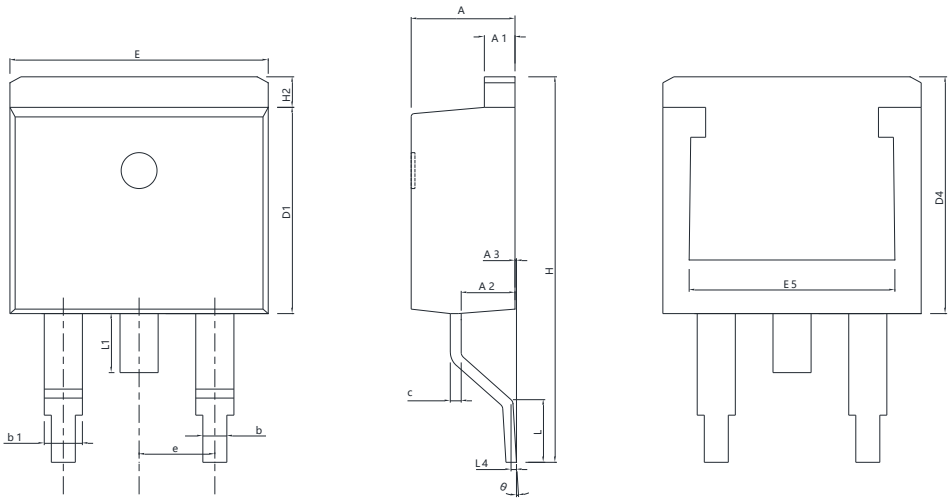


Figure 13. Non-repetitive peak surge forward current versus pulse duration(sinusoidal waveform)

Package Information



Symbol	mm		
	Min	Nom	Max
A	4.37	4.57	4.77
A1	1.22	1.27	1.42
A2	2.49	2.69	2.89
A3	0.00	0.13	0.25
b	0.70	0.81	0.96
b1	1.17	1.27	1.47
c	0.30	0.38	0.53
D1	8.50	8.70	8.90
D4	6.60	-	-
E	9.86	10.16	10.36
E5	7.06	-	-
e	2.54 BSC		
H	14.70	15.10	15.50
H2	1.07	1.27	1.47
L	2.00	2.30	2.60
L1	1.40	1.55	1.70
L4	0.25 BSC		
θ	0°	5°	9°

Version 1: TO263-P package outline dimension

Ordering Information

Package Type	Units/ Reel	Reel / Inner Box	Units/ Inner Box	Inner Boxes/ Carton Box	Units/ Carton Box
TO263-P	800	1	800	5	4000

Product Information

Product	Package	Pb Free	RoHS	Halogen Free
OST25N120KEWF	TO263	yes	yes	yes

Legal Disclaimer

The information given in this document shall in no event be regarded as a guarantee of conditions or characteristics. With respect to any examples or hints given herein, any typical values stated herein and/or any information regarding the application of the device, Oriental Semiconductor hereby disclaims any and all warranties and liabilities of any kind, including without limitation, warranties of non-infringement of intellectual property rights of any third party.

For further information on technology, delivery terms and conditions and prices, please contact the Oriental Semiconductor sales representatives (www.orientalsemi.com).

ORIENTAL SEMICONDUCTOR

A Power Semiconductor Innovator